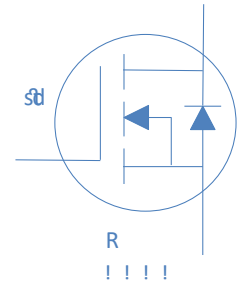
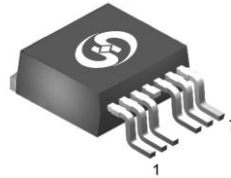


65V N-Ch Power MOSFET

d st d
 ft R ddch d R st R st ft
 D dch ch ch d d ch d st st
 D dch d ftdch drr
 T R dr st ch ft dr st ch
 d ch dd
 st
 R r d st st R R
 ch R st ft ch ft R ddch st
 d r
 T R
 st st

V_{DS}	65	V
$R_{DS(on),typ}$	0.78	m
I_D (Silicon Limited)	506	A
I_D (Package Limited)	240	A

Part Number	Package	Marking
HGB009NE6A	TO-263	GB009NE6A



Absolute Maximum Ratings at T_j

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C	506	A
		T_C	358	
		T_C	240	
Continuous Drain Current (Package Limited)			240	
Drain to Source Voltage	V_{DS}	-	65	V
Gate to Source Voltage	V_{GS}	-	20	V
Pulsed Drain Current	I_{DM}	-	1950	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.4mH, T_C$	720	mJ
Power Dissipation	P_D	T_C	429	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	R	0.35	
Thermal Resistance Junction-Ambient	R	60	



			typ	max
Drain to Source Breakdown Voltage			-	4
			-	1
		$V_{GS}=0V, V_{DS}=60V, T_j$	-	100
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		

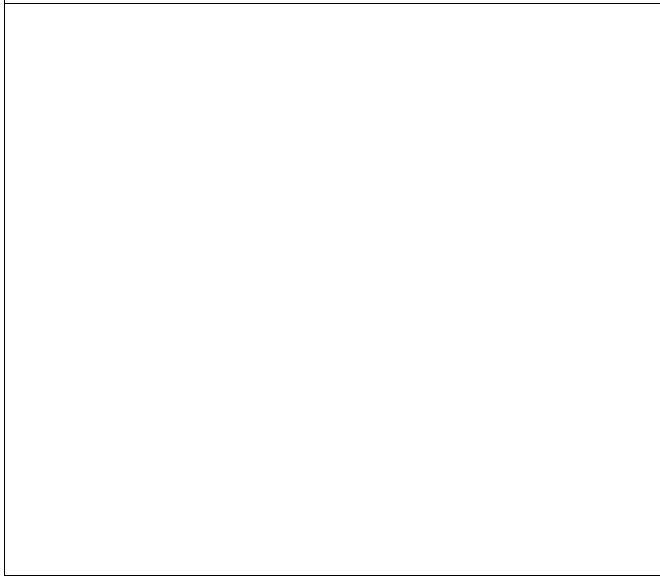
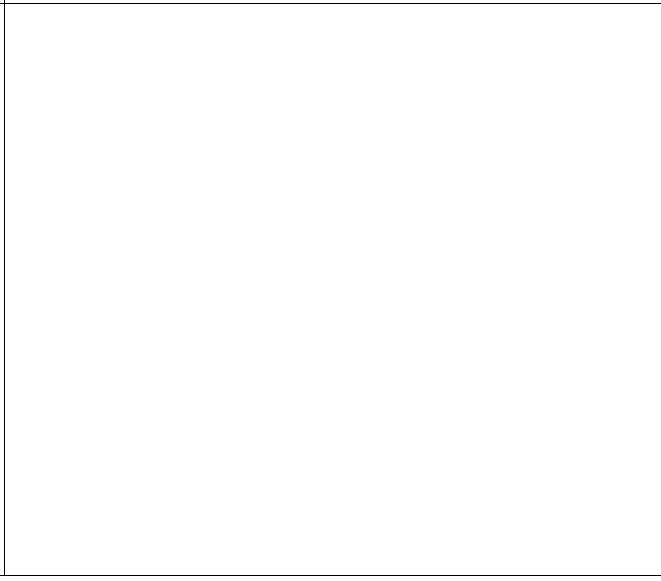
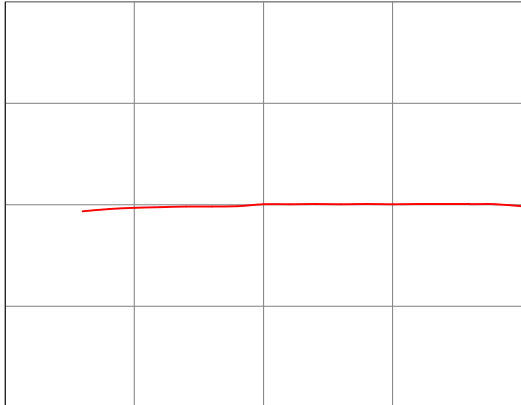

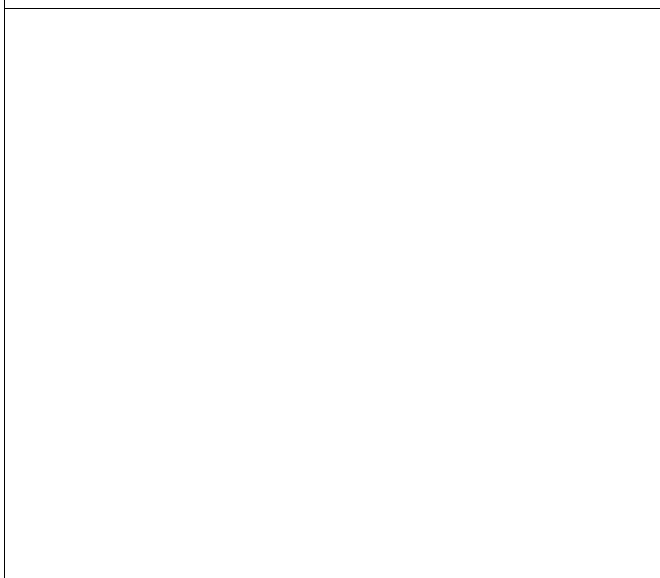
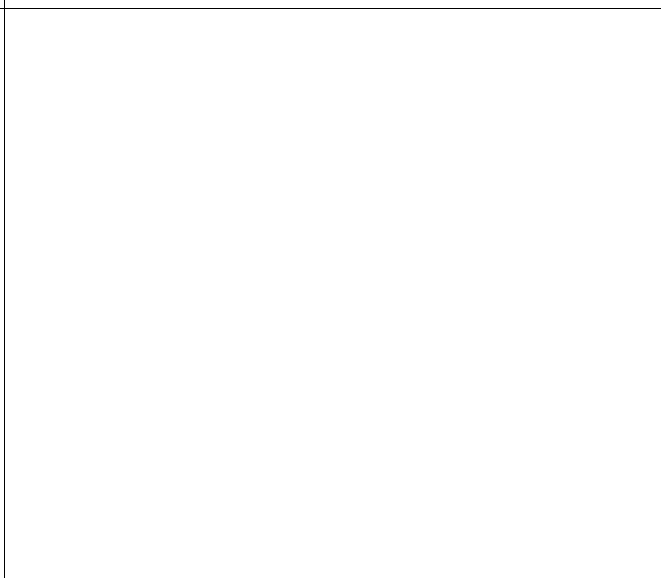
<p>Fig 1. Typical Output Characteristics</p> 	<p>Figure 2. On-Resistance vs. Gate-Source Voltage</p> 
<p>Figure 3. On-Resistance vs. Drain Current and Gate Voltage</p> 	<p>Figure 4. Normalized On-Resistance vs. Junction Temperature</p> 
<p>Figure 5. Typical Transfer Characteristics</p> 	<p>Figure 6. Typical Source-Drain Diode Forward Voltage</p> 

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

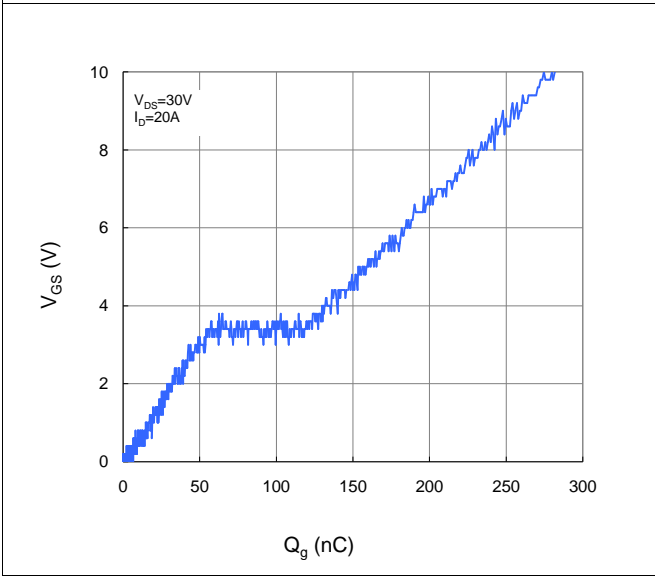


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

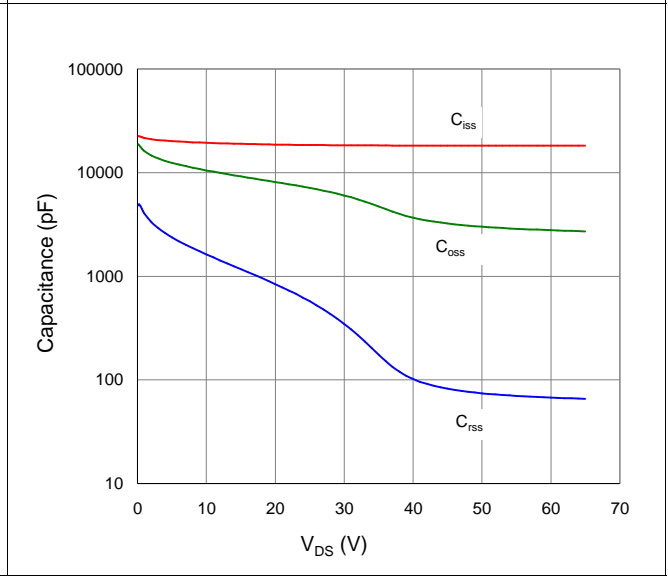


Figure 9. Maximum Safe Operating Area

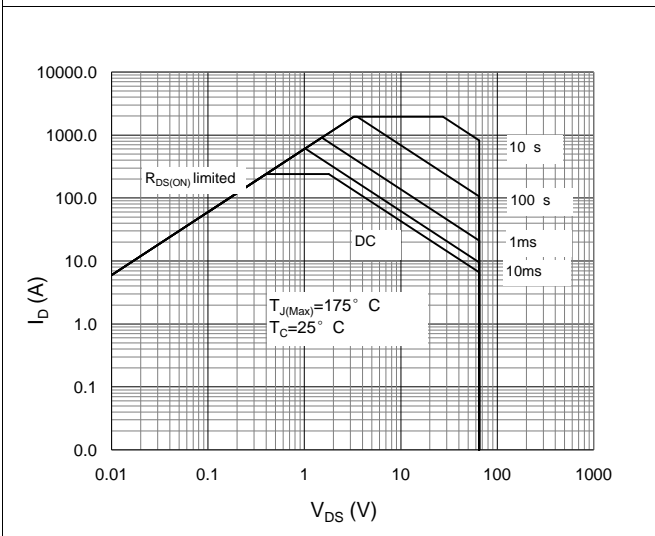


Figure 10. Maximum Drain Current vs. Case Temperature

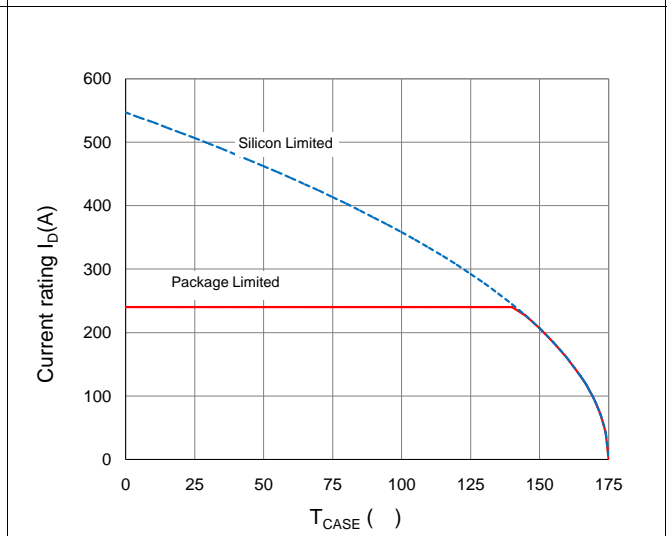
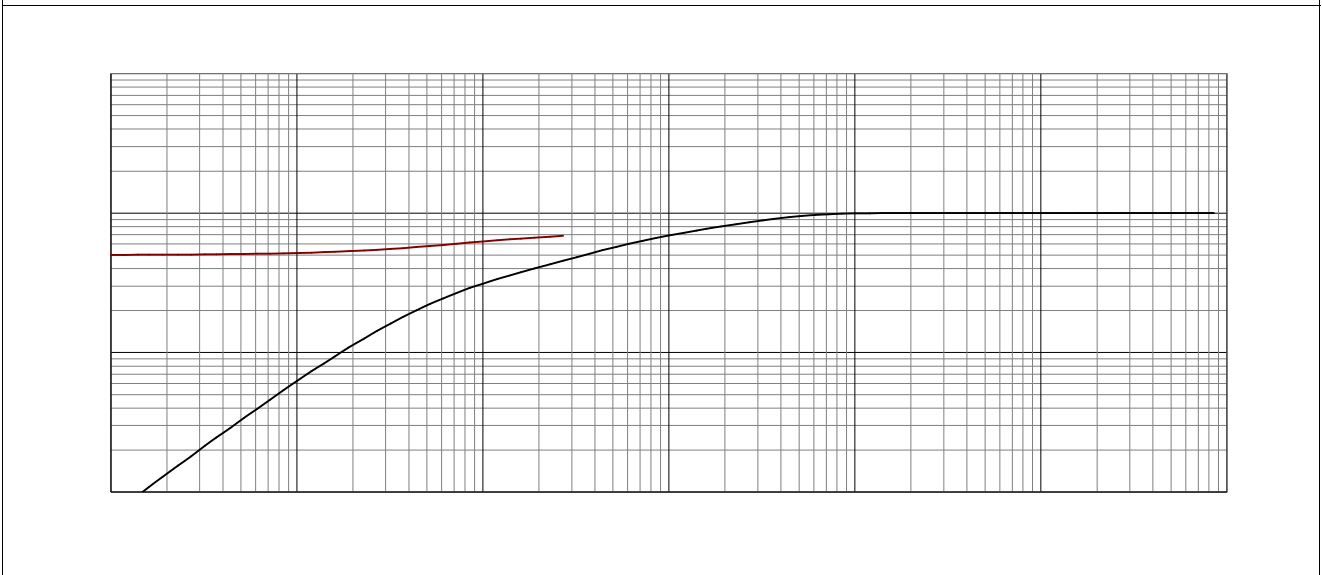
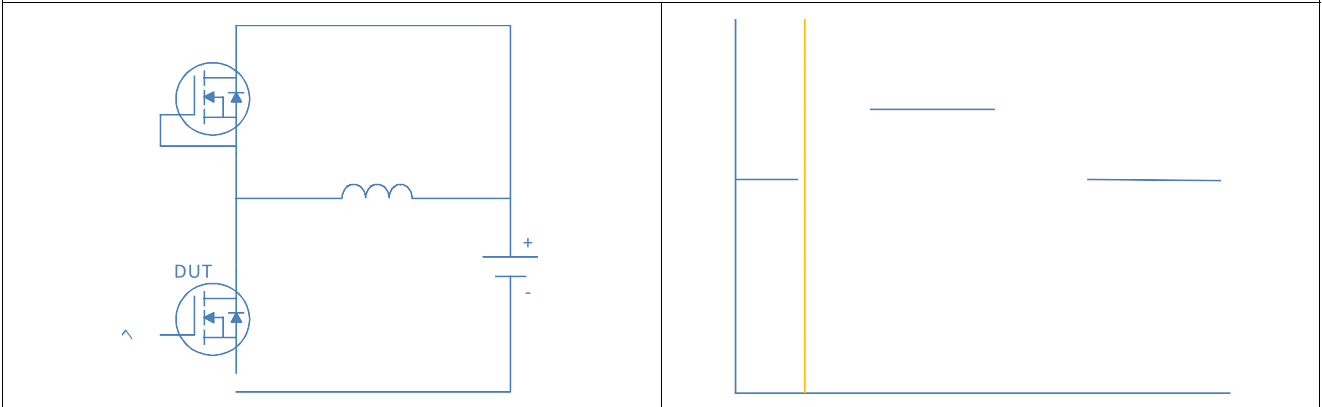


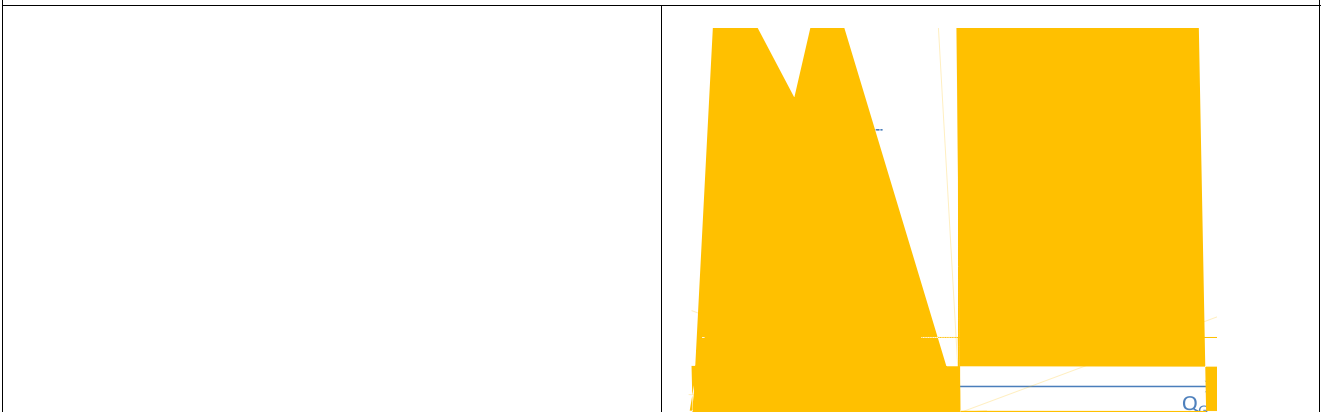
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



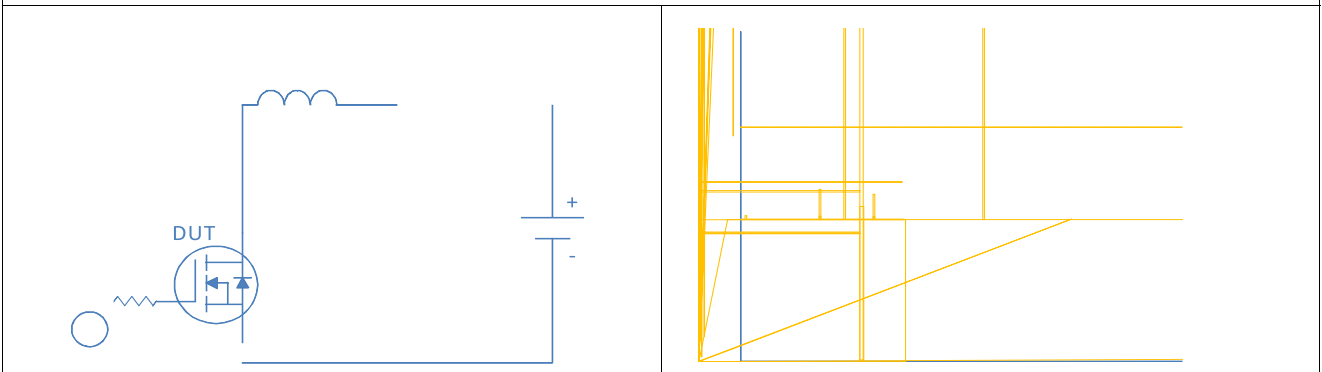
Inductive switching Test



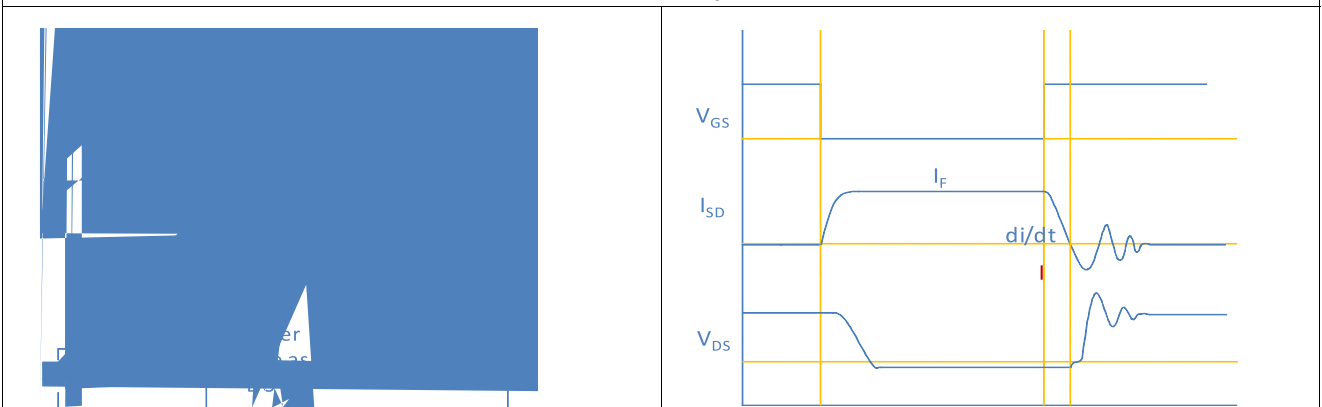
Gate Charge Test



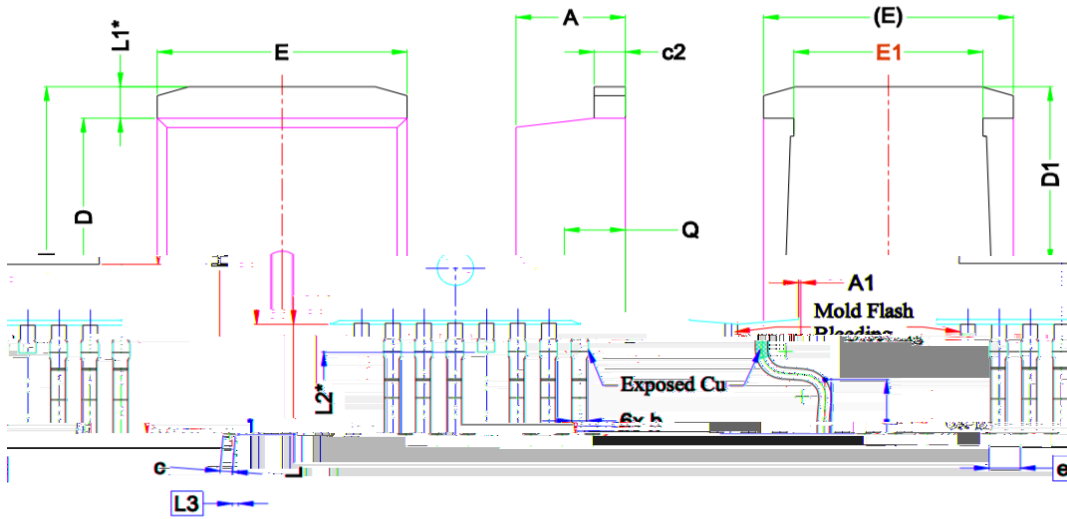
Uclamped Inductive Switching (UIS) Test



Diode Recovery Test



TO-263-7, 7 leads



DIMENSIONS			
MIN.	NOM.	MAX.	SYMBOL
4.24	4.44	4.64	A
0.25	0.10	0.25	A1
0.58	0.80	0.70	B
0.40	0.50	0.60	C
1.15	1.27	1.40	C2
6.82	8.92	6.02	D
6.86	7.65		D1
9.93	10.16	10.36	E
6.89	7.71	7.89	E1
1.27 BSC			e
14.61	15.00	15.38	H
1.78	2.32	2.79	L
1.36 REF.			L1
1.20 REF.			L2
0.25 BSC			L3
0.50		0.25	L3*